

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

NAKAMURA et al

Atty. Ref.: 160-399; Confirmation No.

Appl. No. To be Assigned

Group:

Filed: November 24, 2003

Examiner:

For: NITRIDE SEMICONDUCTOR WITH ACTIVE LAYER OF QUANTUM WELL  
STRUCTURE WITH INDIUM-CONTAINING NITRIDE SEMICONDUCTOR

\* \* \* \* \*

November 24, 2003

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**PRELIMINARY AMENDMENT**

In order to place the above-identified application in better condition for  
examination, please amend the application as follows:

**IN THE TITLE**

Amend the title so that it reads as follows:

NITRIDE SEMICONDUCTOR ~~DEVICE~~ WITH ACTIVE LAYER OF  
QUANTUM WELL STRUCTURE WITH INDIUM-CONTAINING NITRIDE  
SEMICONDUCTOR